

GS1A THRU GS1M

SURFACE MOUNT GLASS PASSIVATED SILICON RECTIFIER

GROWCHILD
ELECTRONICS™

REVERSE VOLTAGE: **50 to 1000 VOLTS**

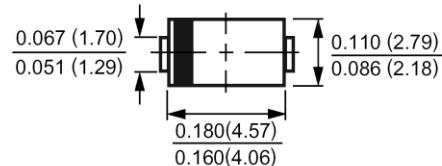
FORWARD CURRENT: **1.0 AMPERE**

<http://www.njzrg.com>

FEATURES

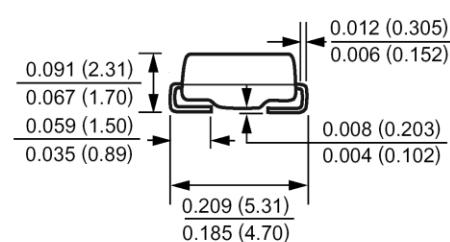
- For surface mounted applications
- Low profile package
- Built-in strain relief
- Easy pick and place
- Low forward voltage drop
- Plastic package has Underwriters Laboratory Flammability Classification 94V-O
- High temperature soldering : 260°C /10 seconds at terminals

DO214-AC(SMA)



MECHANICAL DATA

Case: Molded plastic, DO-214AC(SMA)
 Terminals: Solder plated, solderable per MIL-STD-750, method 2026 guaranteed
 Polarity: Color band denotes cathode end
 Packaging: 12mm tape per EIA STD RS-481
 Weight: 0.002 ounce, 0.064 gram



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25° ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

	Symbols	GS1A	GS1B	GS1D	GS1G	GS1J	GS1K	GS1M	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current at T_L=75	I _(AV)					1.0			Amp
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I _{FSM}					30			Amp
Maximum Forward Voltage at 1.0A	V _F				1.1				Volts
Maximum Reverse Current at T_A=25° at Rated DC Blocking Voltage T_A=125	I _R				5.0				µAmp
Typical Junction Capacitance (Note 1)	C _J				100	12			pF
Typical Thermal Resistance (Note 2)	R _{θJA}					28			/W
Maximum Reverse Recovery Time (Note 3)	T _{RR}					2.5			µS
Operating Junction Temperature Range	T _J				-55 to +150				
Storage Temperature Range	T _{Stg}				-55 to +150				

NOTES:

1- Measured at 1 MHz and applied reverse voltage of 4.0 VDC.

2- Thermal resistance from junction to ambient mounted on P.C.B. with 0.3 x 0.3" (8.0 x 8.0mm) copper pad areas

3- Reverse Recovery Test Conditions : I_F=.5A , I_R=1A , I_{RR}=.25A.

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RATINGS AND CHARACTERISTIC CURVES

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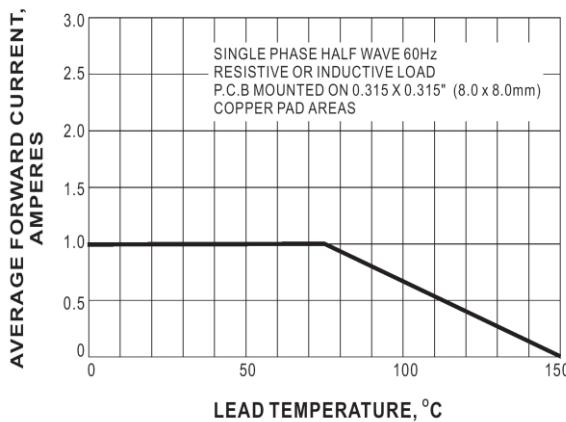


Fig. 1-FORWARD CURRENT DERATING CURVE

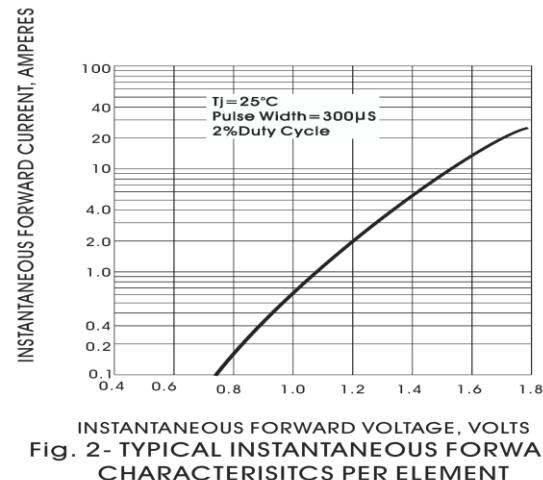


Fig. 2- TYPICAL INSTANTANEOUS FORWARD CHARACTERISITCS PER ELEMENT

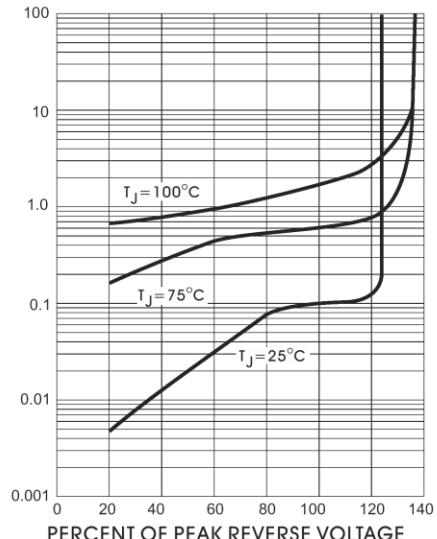


Fig. 3- TYPICAL REAK REVERSE CHARACTERISTICS

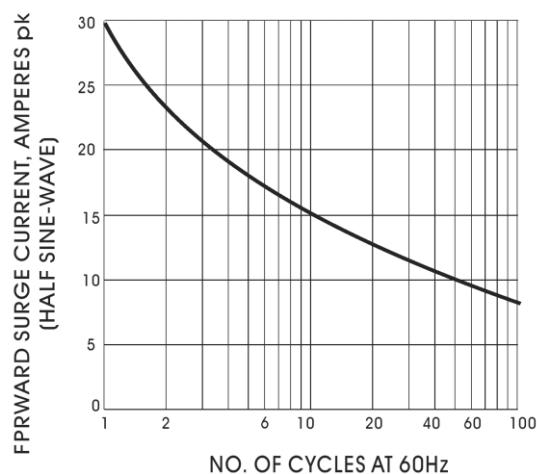


Fig. 4- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

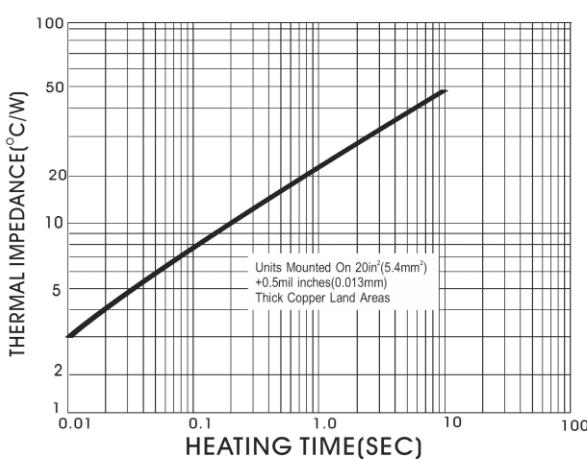


Fig. 5- TRANSIENT THERMAL IMPEDANCE

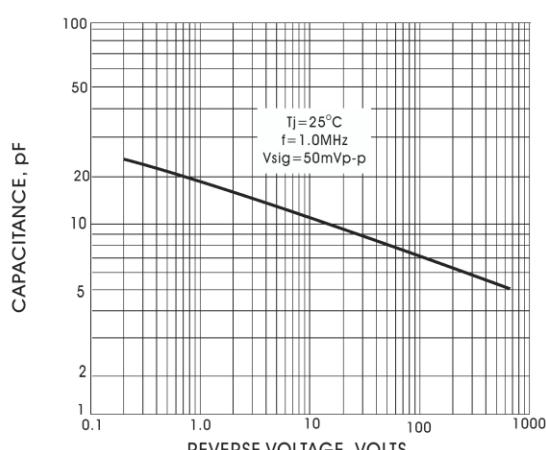


Fig. 6- TYPICL JUNCTION CAPACITANCE PER ELEMENT